

**IN THE CLAIMS:**

Claim 1 (Currently Amended): An in-plane switching liquid crystal display device, comprising:

- a first substrate and a second substrate;
- a gate line and a data line on the first substrate to define a pixel region;
- a floating line including at least two conductive lines adjacent to a lower portion of the data line, wherein a part of the floating line is overlapped with the data line;
- a thin film transistor at an intersection between the gate and data lines;
- a passivation layer on the thin film transistor and the pixel region;
- a common electrode overlapping the data line;
- a pixel electrode separated from the common electrode at a predetermined interval; and
- a liquid crystal layer between the first and second substrates.

Claim 2 (Original): The device according to claim 1, wherein the thin film transistor includes:

- a gate electrode on the first substrate;
- a gate insulating layer on the gate electrode;
- a semiconductor layer on the gate insulating layer;

an ohmic contact layer on the semiconductor layer; and  
source and drain electrodes on the ohmic contact layer.

Claim 3 (Original): The device according to claim 1, further comprising a common line positioned in parallel to the gate line.

Claim 4 (Original): The device according to claim 1, wherein the common electrode and the pixel electrode are formed on a same plane.

Claim 5 (Original): The device according to claim 1, wherein the common electrode and the pixel electrode are formed on the passivation layer.

Claim 6 (Original): The device according to claim 1, wherein the common electrode and the pixel electrode include transparent materials.

Claim 7 (Original): The device according to claim 6, wherein the transparent materials include at least one of indium tin oxide (ITO) and indium zinc oxide (IZO).

Claim 8 (Original): The device according to claim 1, wherein the passivation layer includes at least one of benzocyclobutene (BCB) and acryl.

Claim 9 (Canceled).

Claim 10 (Canceled).

Claim 11 (Original): The device according to claim 10, wherein a width of the floating line is larger than a width of the data line.

Claim 12 (Original): The device according to claim 11, wherein a width of the common electrode is larger than the width of the floating line.

Claim 13 (Original): The device according to claim 1, wherein the floating line and the gate line are simultaneously formed.

Claim 14 (Original): The device according to claim 1, further comprising a black matrix and a color filter on the second substrate.

Claim 15 (Currently Amended): An in-plane switching liquid crystal display device, comprising:

- a first substrate and a second substrate;
- a gate line and a data line on the first substrate to define a pixel region;
- a common line parallel to the gate line;
- a floating line including at least two conductive lines overlapping the data line and formed on a same plane as the gate line;
- a thin film transistor at an intersection between the gate and data lines;
- an organic passivation layer on the thin film transistor and the pixel region;
- a common electrode on the passivation layer overlapping the data line;
- a pixel electrode on the passivation layer to cross the common electrode; and
- a liquid crystal layer between the first and second substrates.

Claim 16 (Currently Amended): A method of fabricating an in-plane switching liquid crystal display device, comprising:

- providing first and second substrates having pixel regions;
- forming a gate line and a floating line including at least two conductive lines on the first substrate;
- forming a data line to overlap the floating line;
- forming a thin film transistor at an intersection of the gate and data lines;

forming a passivation layer on the thin film transistor and the pixel regions;  
forming a common electrode to overlap the data line and a pixel electrode on the passivation layer; and  
forming a liquid crystal layer between the first and second substrates.

Claim 17 (Original): The method according to claim 16, wherein the forming of the thin film transistor includes:

forming a gate electrode on the first substrate;  
forming a gate insulating layer on the gate electrode;  
forming an active layer on the gate insulating layer;  
forming an ohmic contact layer on the active layer to expose a center portion of the active layer; and  
forming source and drain electrodes on the ohmic contact layer.

Claim 18 (Original): The method according to claim 16, further comprising forming a black matrix and a color filter on the second substrate.

Claim 19 (Original): The method according to claim 16, wherein a width of the floating line is larger than a width of the data line.

Claim 20 (Original): The method according to claim 19, wherein a width of the common electrode is larger than the width of the floating line.

Claim 21 (New): The device according to claim 1, wherein the common electrode laterally encircles the pixel electrode.